

Silicon PNP Power Transistors

2SA1147

DESCRIPTION

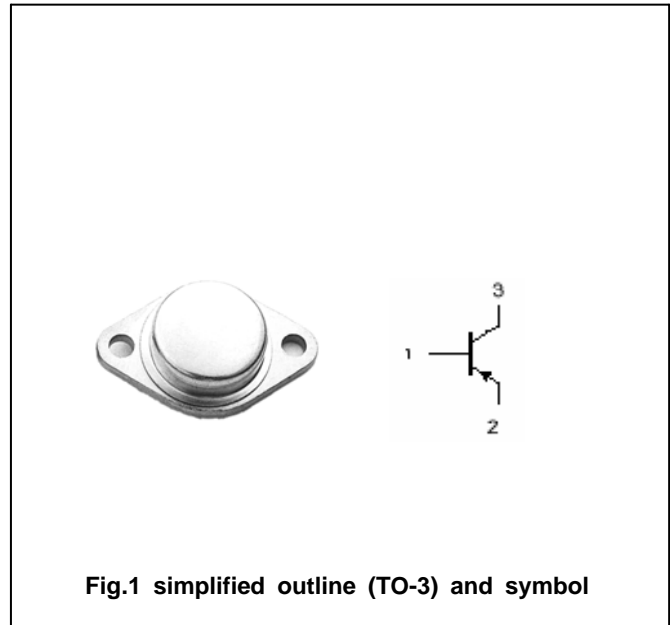
- With TO-3 package
- High power dissipations
- Complement to type 2SC2707

APPLICATIONS

- For power switching amplifier and general purpose applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Absolute maximum ratings(Ta=°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-180	V
V _{CEO}	Collector-emitter voltage	Open base	-180	V
V _{EBO}	Emitter-base voltage	Open collector	-6	V
I _C	Collector current		-15	A
I _B	Base current		-5	A
P _C	Collector power dissipation	T _C =25°C	150	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-65~150	°C

Silicon PNP Power Transistors

2SA1147

CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-50mA ; I _B =0	-180			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-1mA ; I _E =0	-180			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-1mA ; I _C =0	-5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-10A ; I _B =-1A			-3.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-180V ; I _E =0			-0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-6V ; I _C =0			-0.1	mA
h _{FE}	DC current gain	I _C =-5A ; V _{CE} =-4V	30			
f _T	Transition frequency	I _C =-0.5A ; V _{CE} =-12V		60		MHz

PACKAGE OUTLINE

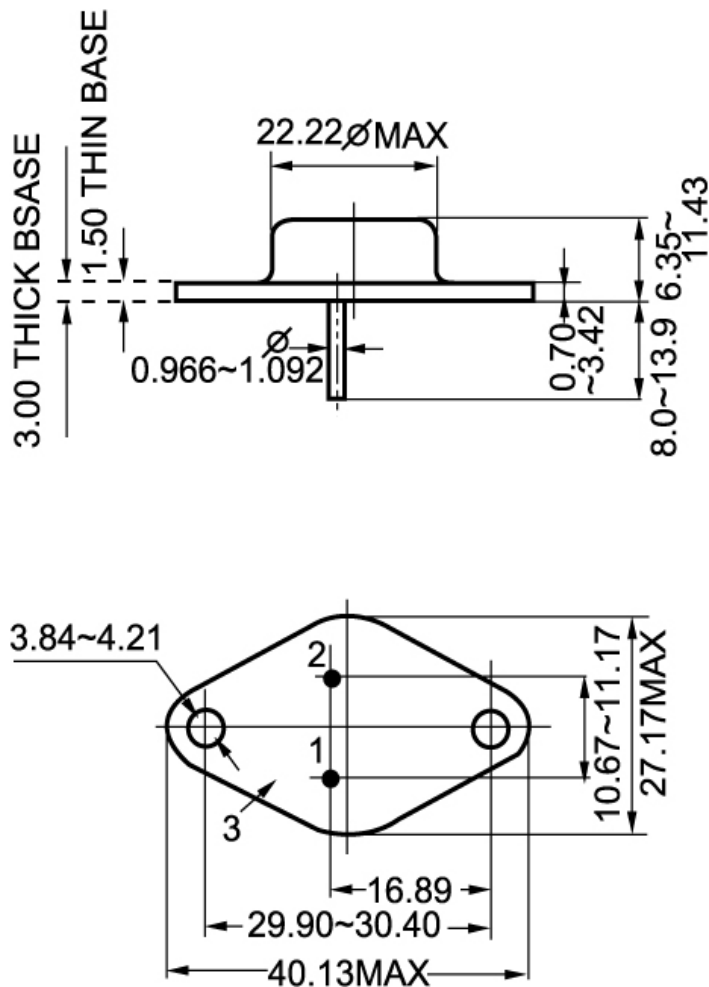


Fig.2 outline dimensions (unindicated tolerance: ± 0.1 mm)